



Welcome to **E-XFL.COM** 

# Understanding <u>Embedded - FPGAs (Field Programmable Gate Array)</u>

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

#### **Applications of Embedded - FPGAs**

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	18432
Number of I/O	71
Number of Gates	60000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-20°C ~ 85°C (TJ)
Package / Case	100-TQFP
Supplier Device Package	100-VQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/a3pn060-zvqg100

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong



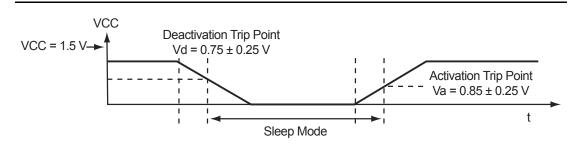


Figure 2-5 • Entering and Exiting Sleep Mode—Typical Timing Diagram

# **Shutdown Mode**

For all ProASIC3/E and ProASIC3 nano devices, shutdown mode can be entered by turning off all power supplies when device functionality is not needed. Cold-sparing and hot-insertion features in ProASIC3 nano devices enable the device to be powered down without turning off the entire system. When power returns, the live at power-up feature enables immediate operation of the device.

# Using Sleep Mode or Shutdown Mode in the System

Depending on the power supply and components used in an application, there are many ways to turn the power supplies connected to the device on or off. For example, Figure 2-6 shows how a microprocessor is used to control a power FET. It is recommended that power FETs with low on resistance be used to perform the switching action.

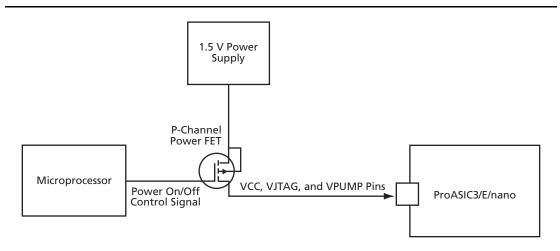


Figure 2-6 • Controlling Power On/Off State Using Microprocessor and Power FET

# **Spine Architecture**

The low power flash device architecture allows the VersaNet global networks to be segmented. Each of these networks contains spines (the vertical branches of the global network tree) and ribs that can reach all the VersaTiles inside its region. The nine spines available in a vertical column reside in global networks with two separate regions of scope: the quadrant global network, which has three spines, and the chip (main) global network, which has six spines. Note that the number of quadrant globals and globals/spines per tree varies depending on the specific device. Refer to Table 3-4 for the clocking resources available for each device. The spines are the vertical branches of the global network tree, shown in Figure 3-3 on page 34. Each spine in a vertical column of a chip (main) global network is further divided into two spine segments of equal lengths: one in the top and one in the bottom half of the die (except in 10 k through 30 k gate devices).

Top and bottom spine segments radiating from the center of a device have the same height. However, just as in the ProASIC family, signals assigned only to the top and bottom spine cannot access the middle two rows of the die. The spines for quadrant clock networks do not cross the middle of the die and cannot access the middle two rows of the architecture.

Each spine and its associated ribs cover a certain area of the device (the "scope" of the spine; see Figure 3-3 on page 34). Each spine is accessed by the dedicated global network MUX tree architecture, which defines how a particular spine is driven—either by the signal on the global network from a CCC, for example, or by another net defined by the user. Details of the chip (main) global network spine-selection MUX are presented in Figure 3-8 on page 44. The spine drivers for each spine are located in the middle of the die.

Quadrant spines can be driven from user I/Os or an internal signal from the north and south sides of the die. The ability to drive spines in the quadrant global networks can have a significant effect on system performance for high-fanout inputs to a design. Access to the top quadrant spine regions is from the top of the die, and access to the bottom quadrant spine regions is from the bottom of the die. The A3PE3000 device has 28 clock trees and each tree has nine spines; this flexible global network architecture enables users to map up to 252 different internal/external clocks in an A3PE3000 device.

Table 3-4 • Globals/Spines/Rows for IGLOO and ProASIC3 Devices

ProASIC3/ ProASIC3L Devices	IGLOO Devices	Chip Globals	Quadrant Globals (4×3)	Clock Trees	Globals/ Spines per Tree	Total Spines per Device	VersaTiles in Each Tree	Total VersaTiles	Rows in Each Spine
A3PN010	AGLN010	4	0	1	0	0	260	260	4
A3PN015	AGLN015	4	0	1	0	0	384	384	6
A3PN020	AGLN020	4	0	1	0	0	520	520	6
A3PN060	AGLN060	6	12	4	9	36	384	1,536	12
A3PN125	AGLN125	6	12	8	9	72	384	3,072	12
A3PN250	AGLN250	6	12	8	9	72	768	6,144	24
A3P015	AGL015	6	0	1	9	9	384	384	12
A3P030	AGL030	6	0	2	9	18	384	768	12
A3P060	AGL060	6	12	4	9	36	384	1,536	12
A3P125	AGL125	6	12	8	9	72	384	3,072	12
A3P250/L	AGL250	6	12	8	9	72	768	6,144	24
A3P400	AGL400	6	12	12	9	108	768	9,216	24
A3P600/L	AGL600	6	12	12	9	108	1,152	13,824	36
A3P1000/L	AGL1000	6	12	16	9	144	1,536	24,576	48
A3PE600/L	AGLE600	6	12	12	9	108	1,120	13,440	35
A3PE1500		6	12	20	9	180	1,888	37,760	59
A3PE3000/L	AGLE3000	6	12	28	9	252	2,656	74,368	83

Global Resources in Low Power Flash Devices

**Using Spines of Occupied Global Networks** 

When a signal is assigned to a global network, the flash switches are programmed to set the MUX select lines (explained in the "Clock Aggregation Architecture" section on page 45) to drive the spines of that network with the global net. However, if the global net is restricted from reaching into the scope of a

For example, if you want to limit the CLK1\_c signal to the left half of the chip and want to use the right side of the same global network for CLK2 c, you can add the following PDC commands:

spine, the MUX drivers of that spine are available for other high-fanout or critical signals (Figure 3-20).

```
define_region -name region1 -type inclusive 0 0 34 29
assign_net_macros region1 CLK1_c
assign_local_clock -net CLK2_c -type chip B2
```

Figure 3-20 • Design Example Using Spines of Occupied Global Networks

# Conclusion

IGLOO, Fusion, and ProASIC3 devices contain 18 global networks: 6 chip global networks and 12 quadrant global networks. These global networks can be segmented into local low-skew networks called spines. The spines provide low-skew networks for the high-fanout signals of a design. These allow you up to 252 different internal/external clocks in an A3PE3000 device. This document describes the architecture for the global network, plus guidelines and methodologies in assigning signals to globals and spines.

# **Related Documents**

### **User's Guides**

IGLOO, ProASIC3, SmartFusion, and Fusion Macro Library Guide http://www.microsemi.com/soc/documents/pa3\_libguide\_ug.pdf



## Global Resources in Low Power Flash Devices

Date	Changes	Page
v1.1 (March 2008)	The "Global Architecture" section was updated to include the IGLOO PLUS family. The bullet was revised to include that the west CCC does not contain a PLL core in 15 k and 30 k devices. Instances of "A3P030 and AGL030 devices" were replaced with "15 k and 30 k gate devices."	31
v1.1 (continued)	Table 3-1 • Flash-Based FPGAs and the accompanying text was updated to include the IGLOO PLUS family. The "IGLOO Terminology" section and "ProASIC3 Terminology" section are new.	32
	The "VersaNet Global Network Distribution" section, "Spine Architecture" section, the note in Figure 3-1 • Overview of VersaNet Global Network and Device Architecture, and the note in Figure 3-3 • Simplified VersaNet Global Network (60 k gates and above) were updated to include mention of 15 k gate devices.	33, 34
	Table 3-4 • Globals/Spines/Rows for IGLOO and ProASIC3 Devices was updated to add the A3P015 device, and to revise the values for clock trees, globals/spines per tree, and globals/spines per device for the A3P030 and AGL030 devices.	41
	Table 3-5 • Globals/Spines/Rows for IGLOO PLUS Devices is new.	42
	CLKBUF_LVCMOS12 was added to Table 3-9 • I/O Standards within CLKBUF.	47
	The "User's Guides" section was updated to include the three different I/O Structures chapters for ProASIC3 and IGLOO device families.	58
v1.0 (January 2008)	Figure 3-3 • Simplified VersaNet Global Network (60 k gates and above) was updated.	34
	The "Naming of Global I/Os" section was updated.	35
	The "Using Global Macros in Synplicity" section was updated.	50
	The "Global Promotion and Demotion Using PDC" section was updated.	51
	The "Designer Flow for Global Assignment" section was updated.	53
	The "Simple Design Example" section was updated.	55
51900087-0/1.05 (January 2005)	Table 3-4 • Globals/Spines/Rows for IGLOO and ProASIC3 Devices was updated.	41

# FlashROM Design Flow

The Microsemi Libero System-on-Chip (SoC) software has extensive FlashROM support, including FlashROM generation, instantiation, simulation, and programming. Figure 5-9 shows the user flow diagram. In the design flow, there are three main steps:

- 1. FlashROM generation and instantiation in the design
- 2. Simulation of FlashROM design
- 3. Programming file generation for FlashROM design

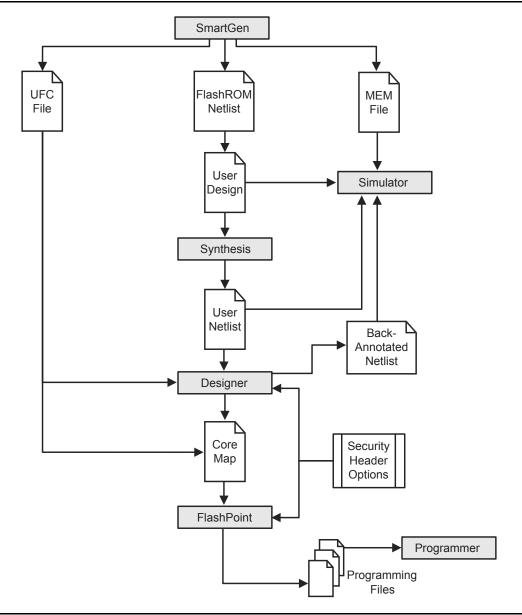


Figure 5-9 • FlashROM Design Flow

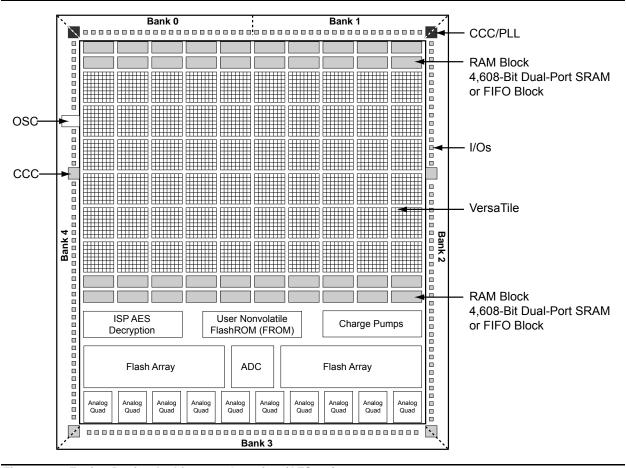


Figure 6-2 • Fusion Device Architecture Overview (AFS600)



# **Cold-Sparing Support**

Cold-sparing refers to the ability of a device to leave system data undisturbed when the system is powered up, while the component itself is powered down, or when power supplies are floating.

Cold-sparing is supported on all IGLOO nano and ProASIC3 nano devices only when the user provides resistors from each power supply to ground. The resistor value is calculated based on the decoupling capacitance on a given power supply. The RC constant should be greater than 3 µs.

To remove resistor current during operation, it is suggested that the resistor be disconnected (e.g., with an NMOS switch) from the power supply after the supply has reached its final value. Refer to the "Power-Up/-Down Behavior of Low Power Flash Devices" section on page 307 for details on cold-sparing.

Cold-sparing means that a subsystem with no power applied (usually a circuit board) is electrically connected to the system that is in operation. This means that all input buffers of the subsystem must present very high input impedance with no power applied so as not to disturb the operating portion of the system.

When targeting low power applications, I/O cold-sparing may add additional current if a pin is configured with either a pull-up or pull-down resistor and driven in the opposite direction. A small static current is induced on each I/O pin when the pin is driven to a voltage opposite to the weak pull resistor. The current is equal to the voltage drop across the input pin divided by the pull resistor. Refer to the "Detailed I/O DC Characteristics" section of the appropriate family datasheet for the specific pull resistor value for the corresponding I/O standard.

For example, assuming an LVTTL 3.3 V input pin is configured with a weak pull-up resistor, a current will flow through the pull-up resistor if the input pin is driven LOW. For LVTTL 3.3 V, the pull-up resistor is ~45 k $\Omega$ , and the resulting current is equal to 3.3 V / 45 k $\Omega$  = 73  $\mu$ A when the I/O pin is driven LOW. This is true also when a weak pull-down is chosen and the input pin is driven HIGH. This current can be avoided by driving the input Low when a weak pull-down resistor is used and driving it HIGH when a weak pull-up resistor is used.

This current draw can occur in the following cases:

- · In Active and Static modes:
  - Input buffers with pull-up, driven Low
  - Input buffers with pull-down, driven High
  - Bidirectional buffers with pull-up, driven Low
  - Bidirectional buffers with pull-down, driven High
  - Output buffers with pull-up, driven Low
  - Output buffers with pull-down, driven High
  - Tristate buffers with pull-up, driven Low
  - Tristate buffers with pull-down, driven High
- In Flash\*Freeze mode (not supported on ProASIC3 nano devices):
  - Input buffers with pull-up, driven Low
  - Input buffers with pull-down, driven High
  - Bidirectional buffers with pull-up, driven Low
  - Bidirectional buffers with pull-down, driven High

ProASIC3 nano FPGA Fabric User's Guide

- The I/O standard of technology-specific I/O macros cannot be changed in the I/O Attribute Editor (see Figure 8-6).
- The user MUST instantiate differential I/O macros (LVDS/LVPECL) in the design. This is the only way to use these standards in the design (IGLOO nano and ProASIC3 nano devices do not support differential inputs).
- To implement the DDR I/O function, the user must instantiate a DDR\_REG or DDR\_OUT macro. This is the only way to use a DDR macro in the design.

Figure 8-6 • Assigning a Different I/O Standard to the Generic I/O Macro

## Performing Place-and-Route on the Design

The netlist created by the synthesis tool should now be imported into Designer and compiled. During Compile, the user can specify the I/O placement and attributes by importing the PDC file. The user can also specify the I/O placement and attributes using ChipPlanner and the I/O Attribute Editor under MVN.

## Defining I/O Assignments in the PDC File

A PDC file is a Tcl script file specifying physical constraints. This file can be imported to and exported from Designer.

Table 8-3 shows I/O assignment constraints supported in the PDC file.

Table 8-3 • PDC I/O Constraints

Command	Action	Example	Comment		
I/O Banks Setting Constraints					
set_iobank	Sets the I/O supply voltage, V <sub>CCI</sub> , and the input reference voltage, V <sub>REF</sub> , for the specified I/O bank.		Must use in case of mixed I/O voltage (V <sub>CCI</sub> ) design		
set_vref	Assigns a V <sub>REF</sub> pin to a bank.	<pre>set_vref -bank [bankname] [pinnum] set_vref -bank Bank0 685 704 723 742 761</pre>	Must use if voltage- referenced I/Os are used		
set_vref_defaults	Sets the default V <sub>REF</sub> pins for the specified bank. This command is ignored if the bank does not need a V <sub>REF</sub> pin.	<pre>set_vref_defaults bankname set_vref_defaults bank2</pre>			

Note: Refer to the Libero SoC User's Guide for detailed rules on PDC naming and syntax conventions.

# 9 – DDR for Microsemi's Low Power Flash Devices

# Introduction

The I/Os in Fusion, IGLOO, and ProASIC3 devices support Double Data Rate (DDR) mode. In this mode, new data is present on every transition (or clock edge) of the clock signal. This mode doubles the data transfer rate compared with Single Data Rate (SDR) mode, where new data is present on one transition (or clock edge) of the clock signal. Low power flash devices have DDR circuitry built into the I/O tiles. I/Os are configured to be DDR receivers or transmitters by instantiating the appropriate special macros (examples shown in Figure 9-4 on page 210 and Figure 9-5 on page 211) and buffers (DDR\_OUT or DDR\_REG) in the RTL design. This document discusses the options the user can choose to configure the I/Os in this mode and how to instantiate them in the design.

# **Double Data Rate (DDR) Architecture**

Low power flash devices support 350 MHz DDR inputs and outputs. In DDR mode, new data is present on every transition of the clock signal. Clock and data lines have identical bandwidths and signal integrity requirements, making them very efficient for implementing very high-speed systems. High-speed DDR interfaces can be implemented using LVDS (not applicable for IGLOO nano and ProASIC3 nano devices). In IGLOOe, ProASIC3E, AFS600, and AFS1500 devices, DDR interfaces can also be implemented using the HSTL, SSTL, and LVPECL I/O standards. The DDR feature is primarily implemented in the FPGA core periphery and is not tied to a specific I/O technology or limited to any I/O standard.

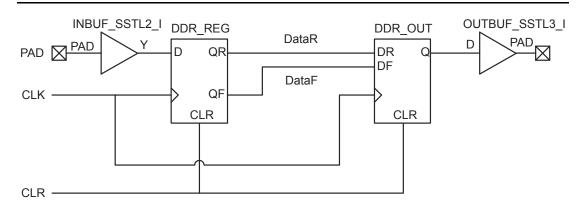


Figure 9-1 • DDR Support in Low Power Flash Devices

DDR for Microsemi's Low Power Flash Devices

# **Design Example**

Figure 9-9 shows a simple example of a design using both DDR input and DDR output registers. The user can copy the HDL code in Libero SoC software and go through the design flow. Figure 9-10 and Figure 9-11 on page 217 show the netlist and ChipPlanner views of the ddr\_test design. Diagrams may vary slightly for different families.

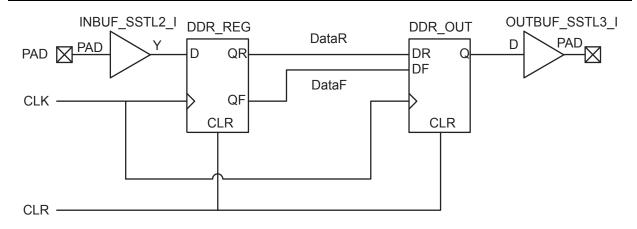


Figure 9-9 • Design Example

Figure 9-10 • DDR Test Design as Seen by NetlistViewer for IGLOO/e Devices

# **General Flash Programming Information**

## **Programming Basics**

When choosing a programming solution, there are a number of options available. This section provides a brief overview of those options. The next sections provide more detail on those options as they apply to Microsemi FPGAs.

## Reprogrammable or One-Time-Programmable (OTP)

Depending on the technology chosen, devices may be reprogrammable or one-time-programmable. As the name implies, a reprogrammable device can be programmed many times. Generally, the contents of such a device will be completely overwritten when it is reprogrammed. All Microsemi flash devices are reprogrammable.

An OTP device is programmable one time only. Once programmed, no more changes can be made to the contents. Microsemi flash devices provide the option of disabling the reprogrammability for security purposes. This combines the convenience of reprogrammability during design verification with the security of an OTP technology for highly sensitive designs.

## Device Programmer or In-System Programming

There are two fundamental ways to program an FPGA: using a device programmer or, if the technology permits, using in-system programming. A device programmer is a piece of equipment in a lab or on the production floor that is used for programming FPGA devices. The devices are placed into a socket mounted in a programming adapter module, and the appropriate electrical interface is applied. The programmed device can then be placed on the board. A typical programmer, used during development, programs a single device at a time and is referred to as a single-site engineering programmer.

With ISP, the device is already mounted onto the system printed circuit board when programming occurs. Typically, ISD programming is performed via a JTAG interface on the FPGA. The JTAG pins can be controlled either by an on-board resource, such as a microprocessor, or by an off-board programmer through a header connection. Once mounted, it can be programmed repeatedly and erased. If the application requires it, the system can be designed to reprogram itself using a microprocessor, without the use of any external programmer.

If multiple devices need to be programmed with the same program, various multi-site programming hardware is available in order to program many devices in parallel. Microsemi In House Programming is also available for this purpose.

# **Programming Features for Microsemi Devices**

#### Flash Devices

The flash devices supplied by Microsemi are reprogrammable by either a generic device programmer or ISP. Microsemi supports ISP using JTAG, which is supported by the FlashPro4 and FlashPro3, FlashPro Lite, Silicon Sculptor 3, and Silicon Sculptor II programmers.

Levels of ISP support vary depending on the device chosen:

- · All SmartFusion, Fusion, IGLOO, and ProASIC3 devices support ISP.
- IGLOO, IGLOOe, IGLOO nano V5, and IGLOO PLUS devices can be programmed in-system when the device is using a 1.5 V supply voltage to the FPGA core.
- IGLOO nano V2 devices can be programmed at 1.2 V core voltage (when using FlashPro4 only) or 1.5 V. IGLOO nano V5 devices are programmed with a VCC core voltage of 1.5 V.



ProASIC3 nano FPGA Fabric User's Guide

2. Choose the appropriate security level setting and enter a FlashLock Pass Key. The default is the **Medium** security level (Figure 11-12). Click **Next**.

If you want to select different options for the FPGA and/or FlashROM, this can be set by clicking **Custom Level**. Refer to the "Advanced Options" section on page 256 for different custom security level options and descriptions of each.

Figure 11-12 • Medium Security Level Selected for Low Power Flash Devices

In-System Programming (ISP) of Microsemi's Low Power Flash Devices Using FlashPro4/3/3X

signal deactivated, which also has the effect of disabling the input buffers. The SAMPLE/PRELOAD instruction captures the status of pads in parallel and shifts them out as new data is shifted in for loading into the Boundary Scan Register (BSR). When the device is in an unprogrammed state, the OE and output BSR will be undefined; however, the input BSR will be defined as long as it is connected and being used. For JTAG timing information on setup, hold, and fall times, refer to the *FlashPro User's Guide*.

# **ISP Support in Flash-Based Devices**

The flash FPGAs listed in Table 12-1 support the ISP feature and the functions described in this document.

Table 12-1 • Flash-Based FPGAs Supporting ISP

Series	Family*	Description
IGLOO	IGL00	Ultra-low power 1.2 V to 1.5 V FPGAs with Flash*Freeze technology
	IGLO0e	Higher density IGLOO FPGAs with six PLLs and additional I/O standards
	IGLOO nano	The industry's lowest-power, smallest-size solution
	IGLOO PLUS	IGLOO FPGAs with enhanced I/O capabilities
ProASIC3	ProASIC3	Low power, high-performance 1.5 V FPGAs
	ProASIC3E	Higher density ProASIC3 FPGAs with six PLLs and additional I/O standards
	ProASIC3 nano	Lowest-cost solution with enhanced I/O capabilities
	ProASIC3L	ProASIC3 FPGAs supporting 1.2 V to 1.5 V with Flash*Freeze technology
	RT ProASIC3	Radiation-tolerant RT3PE600L and RT3PE3000L
	Military ProASIC3/EL	Military temperature A3PE600L, A3P1000, and A3PE3000L
	Automotive ProASIC3	ProASIC3 FPGAs qualified for automotive applications
SmartFusion	SmartFusion	Mixed signal FPGA integrating ProASIC3 FPGA fabric, programmable microcontroller subsystem (MSS) which includes programmable analog and an ARM® Cortex™-M3 hard processor and flash memory in a monolithic device
Fusion	Fusion	Mixed signal FPGA integrating ProASIC3 FPGA fabric, programmable analog block, support for ARM <sup>®</sup> Cortex™-M1 soft processors, and flash memory into a monolithic device
ProASIC	ProASIC	First generation ProASIC devices
	ProASIC <sup>PLUS</sup>	Second generation ProASIC devices

Note: \*The device names link to the appropriate datasheet, including product brief, DC and switching characteristics, and packaging information.

#### IGLOO Terminology

In documentation, the terms IGLOO series and IGLOO devices refer to all of the IGLOO devices as listed in Table 12-1. Where the information applies to only one product line or limited devices, these exclusions will be explicitly stated.

# **ProASIC3 Terminology**

In documentation, the terms ProASIC3 series and ProASIC3 devices refer to all of the ProASIC3 devices as listed in Table 12-1. Where the information applies to only one product line or limited devices, these exclusions will be explicitly stated.

To further understand the differences between the IGLOO and ProASIC3 devices, refer to the *Industry's Lowest Power FPGAs Portfolio*.



In-System Programming (ISP) of Microsemi's Low Power Flash Devices Using FlashPro4/3/3X

errors, but this list is intended to show where problems can occur. FlashPro4/3/3X allows TCK to be lowered from 6 MHz down to 1 MHz to allow you to address some signal integrity problems that may occur with impedance mismatching at higher frequencies. Customers are expected to troubleshoot board-level signal integrity issues by measuring voltages and taking scope plots.

#### Scan Chain Failure

Normally, the FlashPro4/3/3X Scan Chain command expects to see 0x1 on the TDO pin. If the command reports reading 0x0 or 0x3, it is seeing the TDO pin stuck at 0 or 1. The only time the TDO pin comes out of tristate is when the JTAG TAP state machine is in the Shift-IR or Shift-DR state. If noise or reflections on the TCK or TMS lines have disrupted the correct state transitions, the device's TAP state controller might not be in one of these two states when the programmer tries to read the device. When this happens, the output is floating when it is read and does not match the expected data value. This can also be caused by a broken TDO net. Only a small amount of data is read from the device during the Scan Chain command, so marginal problems may not always show up during this command. Occasionally a faulty programmer can cause intermittent scan chain failures.

#### Exit 11

This error occurs during the verify stage of programming a device. After programming the design into the device, the device is verified to ensure it is programmed correctly. The verification is done by shifting the programming data into the device. An internal comparison is performed within the device to verify that all switches are programmed correctly. Noise induced by poor signal integrity can disrupt the writes and reads or the verification process and produce a verification error. While technically a verification error, the root cause is often related to signal integrity.

Refer to the *FlashPro User's Guide* for other error messages and solutions. For the most up-to-date known issues and solutions, refer to http://www.microsemi.com/soc/support.

# Conclusion

IGLOO, ProASIC3, SmartFusion, and Fusion devices offer a low-cost, single-chip solution that is live at power-up through nonvolatile flash technology. The FlashLock Pass Key and 128-bit AES Key security features enable secure ISP in an untrusted environment. On-chip FlashROM enables a host of new applications, including device serialization, subscription-based applications, and IP addressing. Additionally, as the FlashROM is nonvolatile, all of these services can be provided without battery backup.

# **Related Documents**

#### User's Guides

FlashPro User's Guide

http://www.microsemi.com/soc/documents/flashpro\_ug.pdf



Core Voltage Switching Circuit for IGLOO and ProASIC3L In-System Programming

3. VCC switches from 1.5 V to 1.2 V when TRST is LOW.

#### Figure 13-4 • TRST Toggled LOW

In Figure 13-4, the TRST signal and the VCC core voltage signal are labeled. As TRST is pulled to ground, the core voltage is observed to switch from  $1.5\,\mathrm{V}$  to  $1.2\,\mathrm{V}$ . The observed fall time is approximately  $2\,\mathrm{ms}$ .

## **DirectC**

The above analysis is based on FlashPro3, but there are other solutions to ISP, such as DirectC is a microprocessor program that can be run in-system to program Microsemi flash devices. For FlashPro3, TRST is the most convenient control signal to use for the recommended circuit. However, for DirectC, users may use any signal to control the FET. For example, the DirectC code can be edited so that a separate non-JTAG signal can be asserted from the microcontroller that signals the board that it is about to start programming the device. After asserting the N-Channel Digital FET control signal, the programming algorithm must allow sufficient time for the supply to rise to 1.5 V before initiating DirectC programming. As seen in Figure 13-3 on page 279, 50 ms is adequate time. Depending on the size of the PCB and the capacitance on the VCC supply, results may vary from system to system. Microsemi recommends using a conservative value for the wait time to make sure that the VCC core voltage is at the right level.

# Conclusion

For applications using IGLOO and ProASIC3L low power FPGAs and taking advantage of the low core voltage power supplies with less than 1.5 V operation, there must be a way for the core voltage to switch from 1.2 V (or other voltage) to 1.5 V, which is required during in-system programming. The circuit explained in this document illustrates one simple, cost-effective way of handling this requirement. A JTAG signal from the FlashPro3 programmer allows the circuit to sense when programming is in progress, enabling it to switch to the correct core voltage.

# 14 – Microprocessor Programming of Microsemi's Low Power Flash Devices

# Introduction

The Fusion, IGLOO, and ProASIC3 families of flash FPGAs support in-system programming (ISP) with the use of a microprocessor. Flash-based FPGAs store their configuration information in the actual cells within the FPGA fabric. SRAM-based devices need an external configuration memory, and hybrid nonvolatile devices store the configuration in a flash memory inside the same package as the SRAM FPGA. Since the programming of a true flash FPGA is simpler, requiring only one stage, it makes sense that programming with a microprocessor in-system should be simpler than with other SRAM FPGAs. This reduces bill-of-materials costs and printed circuit board (PCB) area, and increases system reliability.

Nonvolatile flash technology also gives the low power flash devices the advantage of a secure, low power, live-at-power-up, and single-chip solution. Low power flash devices are reprogrammable and offer time-to-market benefits at an ASIC-level unit cost. These features enable engineers to create high-density systems using existing ASIC or FPGA design flows and tools.

This document is an introduction to microprocessor programming only. To explain the difference between the options available, user's guides for DirectC and STAPL provide more detail on implementing each style.

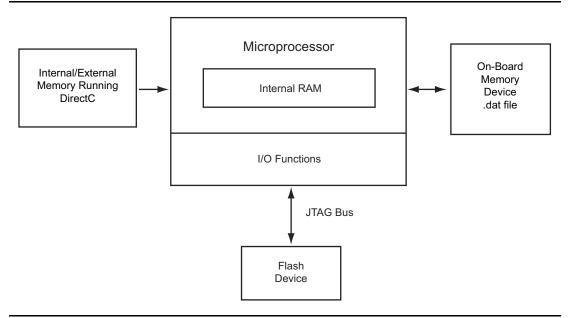


Figure 14-1 • ISP Using Microprocessor



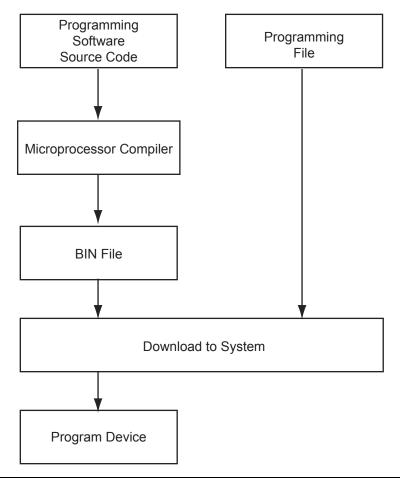


Figure 14-3 • MCU FPGA Programming Model

#### **FlashROM**

Microsemi low power flash devices have 1 kbit of user-accessible, nonvolatile, FlashROM on-chip. This nonvolatile FlashROM can be programmed along with the core or on its own using the standard IEEE 1532 JTAG programming interface.

The FlashROM is architected as eight pages of 128 bits. Each page can be individually programmed (erased and written). Additionally, on-chip AES security decryption can be used selectively to load data securely into the FlashROM (e.g., over public or private networks, such as the Internet). Refer to the "FlashROM in Microsemi's Low Power Flash Devices" section on page 117.

#### STAPL vs. DirectC

Programming the low power flash devices is performed using DirectC or the STAPL player. Both tools use the STAPL file as an input. DirectC is a compiled language, whereas STAPL is an interpreted language. Microprocessors will be able to load the FPGA using DirectC much more quickly than STAPL. This speed advantage becomes more apparent when lower clock speeds of 8- or 16-bit microprocessors are used. DirectC also requires less memory than STAPL, since the programming algorithm is directly implemented. STAPL does have one advantage over DirectC—the ability to upgrade. When a new programming algorithm is required, the STAPL user simply needs to regenerate a STAPL file using the latest version of the Designer software and download it to the system. The DirectC user must download the latest version of DirectC from Microsemi, compile everything, and download the result into the system (Figure 14-4).

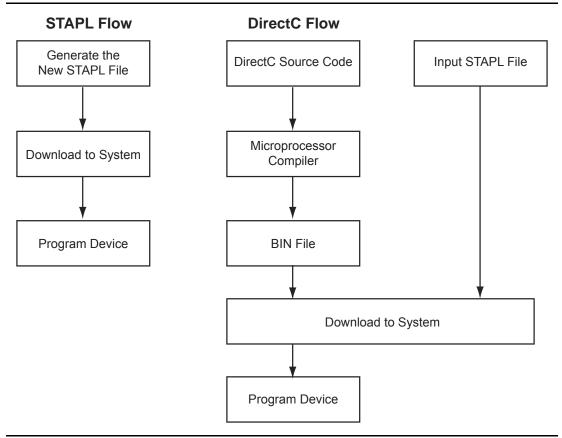


Figure 14-4 • STAPL vs. DirectC

Microprocessor Programming of Microsemi's Low Power Flash Devices

# Remote Upgrade via TCP/IP

Transmission Control Protocol (TCP) provides a reliable bitstream transfer service between two endpoints on a network. TCP depends on Internet Protocol (IP) to move packets around the network on its behalf. TCP protects against data loss, data corruption, packet reordering, and data duplication by adding checksums and sequence numbers to transmitted data and, on the receiving side, sending back packets and acknowledging the receipt of data.

The system containing the low power flash device can be assigned an IP address when deployed in the field. When the device requires an update (core or FlashROM), the programming instructions along with the new programming data (AES-encrypted cipher text) can be sent over the Internet to the target system via the TCP/IP protocol. Once the MCU receives the instruction and data, it can proceed with the FPGA update. Low power flash devices support Message Authentication Code (MAC), which can be used to validate data for the target device. More details are given in the "Message Authentication Code (MAC) Validation/Authentication" section.

# **Hardware Requirement**

To facilitate the programming of the low power flash families, the system must have a microprocessor (with access to the device JTAG pins) to process the programming algorithm, memory to store the programming algorithm, programming data, and the necessary programming voltage. Refer to the relevant datasheet for programming voltages.

# **Security**

# **Encrypted Programming**

As an additional security measure, the devices are equipped with AES decryption. AES works in two steps. The first step is to program a key into the devices in a secure or trusted programming center (such as Microsemi SoC Products Group In-House Programming (IHP) center). The second step is to encrypt any programming files with the same encryption key. The encrypted programming file will only work with the devices that have the same key. The AES used in the low power flash families is the 128-bit AES decryption engine (Rijndael algorithm).

# Message Authentication Code (MAC) Validation/Authentication

As part of the AES decryption flow, the devices are equipped with a MAC validation/authentication system. MAC is an authentication tag, also called a checksum, derived by applying an on-chip authentication scheme to a STAPL file as it is loaded into the FPGA. MACs are computed and verified with the same key so they can only be verified by the intended recipient. When the MCU system receives the AES-encrypted programming data (cipher text), it can validate the data by loading it into the FPGA and performing a MAC verification prior to loading the data, via a second programming pass, into the FPGA core cells. This prevents erroneous or corrupt data from getting into the FPGA.

Low power flash devices with AES and MAC are superior to devices with only DES or 3DES encryption. Because the MAC verifies the correctness of the data, the FPGA is protected from erroneous loading of invalid programming data that could damage a device (Figure 14-5 on page 289).

The AES with MAC enables field updates over public networks without fear of having the design stolen. An encrypted programming file can only work on devices with the correct key, rendering any stolen files



# Summary of Changes

Revision (month/year)	Chapter Affected	List of Changes (page number)
Revision 1 (continued)	"In-System Programming (ISP) of Microsemi's Low Power Flash Devices Using FlashPro4/3/3X" was revised.	273
	"Core Voltage Switching Circuit for IGLOO and ProASIC3L In-System Programming" was revised.	281
	"Boundary Scan in Low Power Flash Devices" was revised.	296
Revision 0 (April 2010)	The ProASIC3 nano Low Power Flash FPGAs Handbook was divided into two parts to create the ProASIC3 nano Datasheet ProASIC3 nano Device Family User's Guide.	